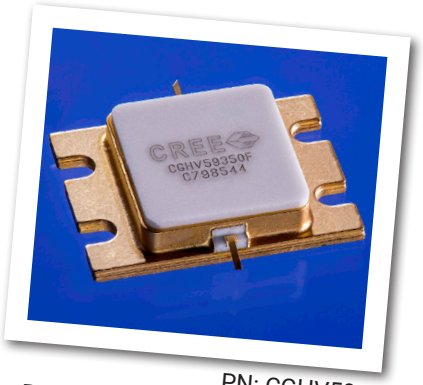
CGHV59350

350 W, 5200 - 5900 MHz, 50-Ohm Input/Output Matched, GaN HEMT for C-Band Radar Systems

Cree's CGHV59350 is a gallium nitride (GaN) high electron mobility transistor (HEMT) designed specifically with high efficiency, high gain and wide bandwidth capabilities, which makes the CGHV59350 ideal for 5.2 - 5.9 GHz C-Band radar amplifier applications. The transistor is supplied in a ceramic/metal flange package, type 440217 and 440218.



PN: CGHV59350
Package Type: 440217 and 440218

Typical Performance Over 5.2 - 5.9 GHz (T_C = 25°C) of Demonstration Amplifier

Parameter	5.2 GHz	5.55 GHz	5.9 GHz	Units
Output Power	440	445	490	W
Gain	10.5	10.5	11	dB
Drain Efficiency	59	54	55	%

Note:
Measured in the CGHV59350-TB under 100 µs pulse width, 10% duty cycle, P_{IN} = 46 dBm

Features

- 5.2 - 5.9 GHz Operation
- 450 W Typical Output Power
- 10.5 dB Power Gain
- 55% Typical Drain Efficiency
- 50 Ohm Internally Matched
- <0.3 dB Pulsed Amplitude Droop

Absolute Maximum Ratings (not simultaneous)

Parameter	Symbol	Rating	Units	Conditions
Pulse Width	PW	100	µs	
Duty Cycle	DC	10	%	
Drain-Source Voltage	V_{DSS}	125	Volts	25˚C
Gate-to-Source Voltage	V_{GS}	-10, +2	Volts	25˚C
Storage Temperature	T_{STG}	-65, +150	˚C	
Operating Junction Temperature	T_J	225	˚C	
Maximum Forward Gate Current	I_{GMAX}	64	mA	25˚C
Maximum Drain Current[1]	I_{DMAX}	24	A	25˚C
Soldering Temperature[2]	T_S	245	˚C	
Screw Torque	τ	40	in-oz	
Pulsed Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.31	˚C/W	100 µsec, 10%, 85˚C , P_{DISS} = 320 W
Case Operating Temperature	T_C	-40, +85	˚C	

Notes:
[1] Current limit for long term, reliable operation
[2] Refer to the Application Note on soldering at http://www.cree.com/rf/tools-and-support/document-library

Electrical Characteristics

Characteristics	Symbol	Min.	Typ.	Max.	Units	Conditions
DC Characteristics[1] (T_C = 25˚C)						
Gate Threshold Voltage	$V_{GS(th)}$	-3.8	-3.0	-2.3	V_{DC}	V_{DS} = 10 V, I_D = 64 mA
Gate Quiescent Voltage	$V_{GS(Q)}$	–	-2.7	–	V_{DC}	V_{DS} = 50 V, I_D = 1.0 A
Saturated Drain Current[2]	I_{DS}	48	57.8	–	A	V_{DS} = 6.0 V, V_{GS} = 2.0 V
Drain-Source Breakdown Voltage	V_{BR}	150	–	–	V_{DC}	V_{GS} = -8 V, I_D = 64 mA

Notes:
[1] Measured on wafer prior to packaging.
[2] Scaled from PCM data.

Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
www.cree.com/rf

Electrical Characteristics Continued...

Characteristics	Symbol	Min.	Typ.	Max.	Units	Conditions
RF Characteristics[3] (T_C = 25°C, F_0 = 5.2 - 5.9 GHz unless otherwise noted)						
Output Power at 5.2 GHz	P_{OUT1}	–	440	–	W	V_{DD} = 50 V, I_{DQ} = 1 A, P_{IN} = 46 dBm
Output Power at 5.55 GHz	P_{OUT2}	–	445	–	W	V_{DD} = 50 V, I_{DQ} = 1 A, P_{IN} = 46 dBm
Output Power at 5.9 GHz	P_{OUT3}	–	490	–	W	V_{DD} = 50 V, I_{DQ} = 1 A, P_{IN} = 46 dBm
Gain at 5.2 GHz	G_{P1}	–	10.5	–	dB	V_{DD} = 50 V, I_{DQ} = 1 A, P_{IN} = 46 dBm
Gain at 5.55 GHz	G_{P2}	–	10.5	–	dB	V_{DD} = 50 V, I_{DQ} = 1 A, P_{IN} = 46 dBm
Gain at 5.9 GHz	G_{P3}	–	11	–	dB	V_{DD} = 50 V, I_{DQ} = 1 A, P_{IN} = 46 dBm
Drain Efficiency at 5.2 GHz	D_{E1}	–	59	–	%	V_{DD} = 50 V, I_{DQ} = 1 A, P_{IN} = 46 dBm
Drain Efficiency at 5.55 GHz	D_{E2}	–	54	–	%	V_{DD} = 50 V, I_{DQ} = 1 A, P_{IN} = 46 dBm
Drain Efficiency at 5.9 GHz	D_{E3}	–	55	–	%	V_{DD} = 50 V, I_{DQ} = 1 A, P_{IN} = 46 dBm
Small Signal Gain	S21	–	15	–	dB	V_{DD} = 50 V, I_{DQ} = 1 A, P_{IN} = -10 dBm
Input Return Loss	S11	–	-7	–	dB	V_{DD} = 50 V, I_{DQ} = 1 A, P_{IN} = -10 dBm
Output Return Loss	S22	–	-11	–	dB	V_{DD} = 50 V, I_{DQ} = 1 A, P_{IN} = -10 dBm
Amplitude Droop	D	–	-0.3	–	dB	V_{DD} = 50 V, I_{DQ} = 1 A, P_{IN} = 46 dBm
Output Stress Match	VSWR	–	5:1	–	Ψ	No damage at all phase angles, V_{DD} = 50 V, I_{DQ} = 1 A, P_{IN} = 46 dBm Pulsed

Notes:
[3] Measured in CGHV59350-TB. Pulse Width = 100 µS, Duty Cycle = 10%.

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Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
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Typical Performance

Figure 1. - Small Signal S-Parameters
CGHV59350 in Test Fixture
V_{DD} = 50 V, I_{DQ} = 1 A, T_{case} = 25 °C

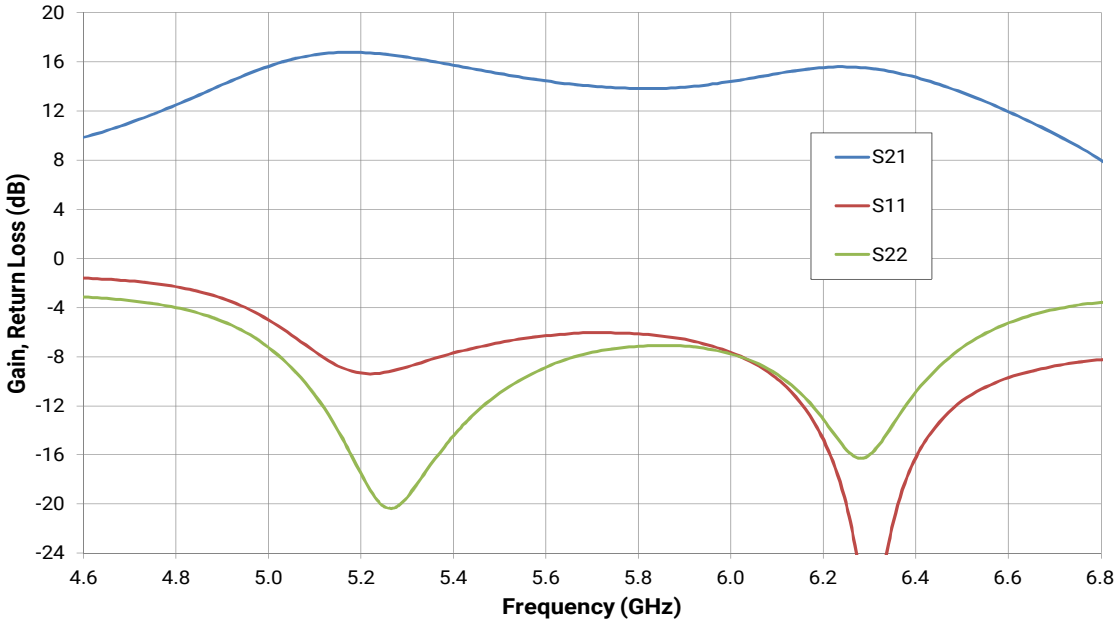
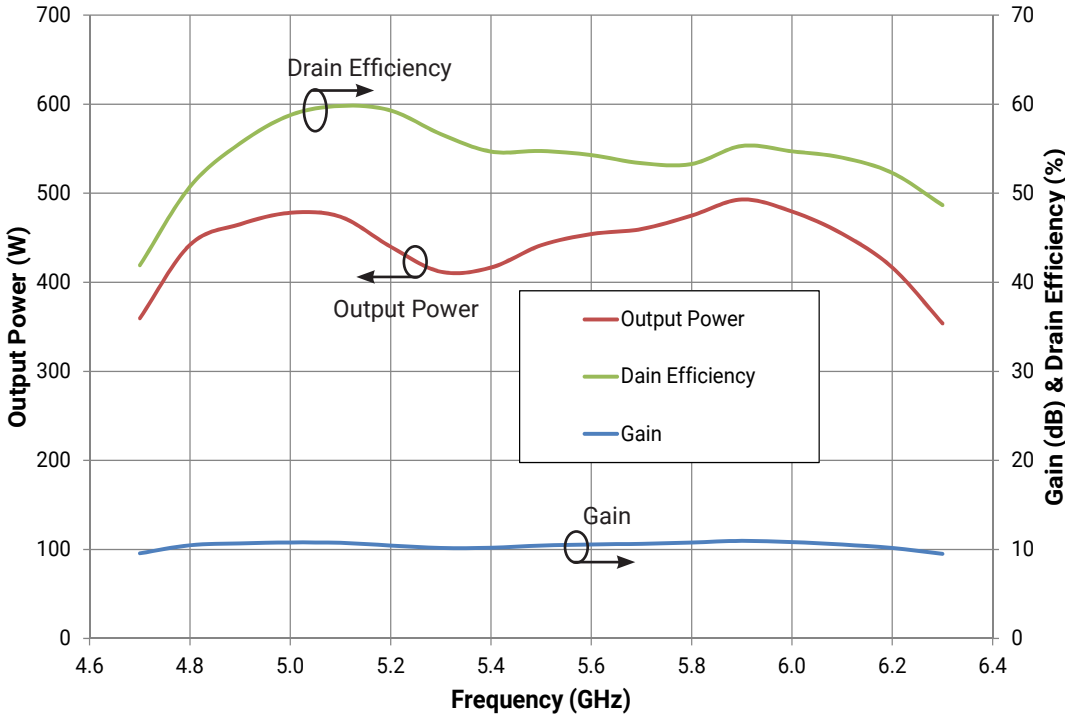


Figure 2. - CGHV59350 Pout, D_{Eff}, and Gain vs. Frequency at T_{case} = 25 °C
V_{DD} = 50V, I_{DQ}=1.0 A, P_{IN}=46 dBm, Pulse Width = 100µS, Duty Cycle = 10%



Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
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Typical Performance

Figure 3. - CGHV59350 Output Power vs. Input Power

V_{DD} = 50V, I_{DQ}= 1.0 A, Pulse Width = 100µS, Duty Cycle = 10%, T_{case} = 25 °C

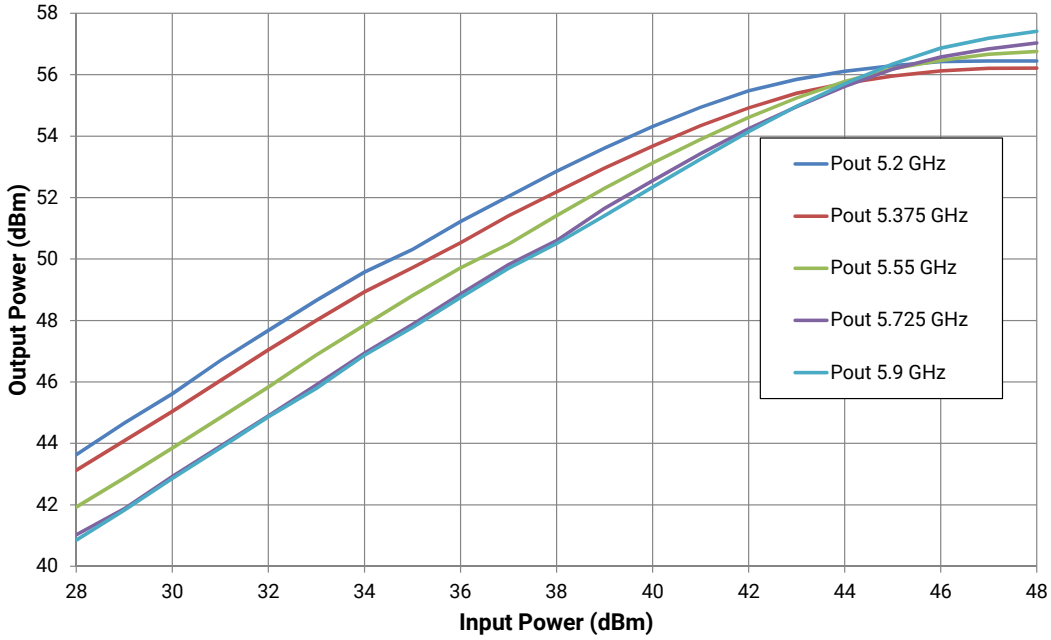
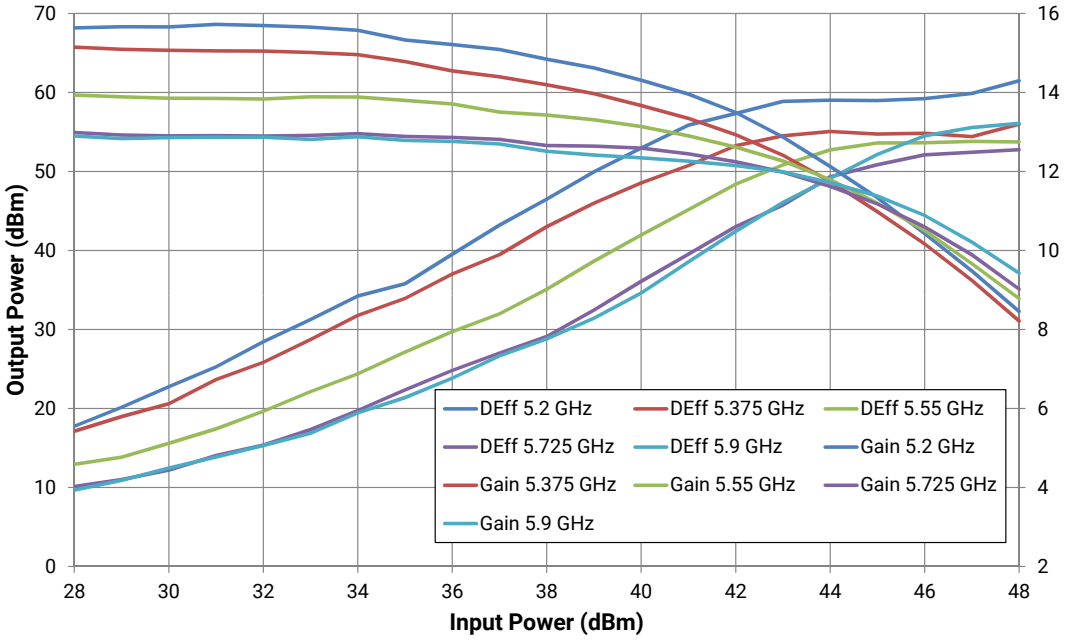


Figure 4. - CGHV59350 Output Power vs. Input Power

V_{DD} = 50V, I_{DQ}= 1.0 A, Pulse Width = 100µS, Duty Cycle = 10%, T_{case} = 25 °C



Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
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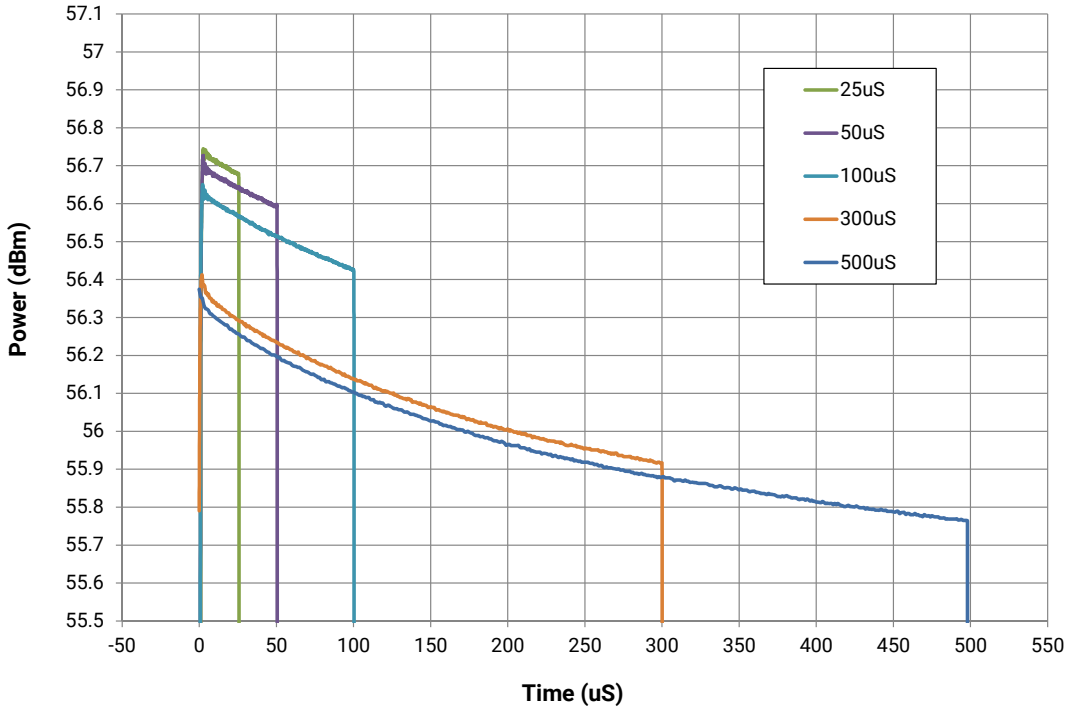
Typical Performance

Figure 5. - Output Power vs. Time
V_{DD} = 50V, P_{IN}=46 dBm, Duty Cycle = 10%



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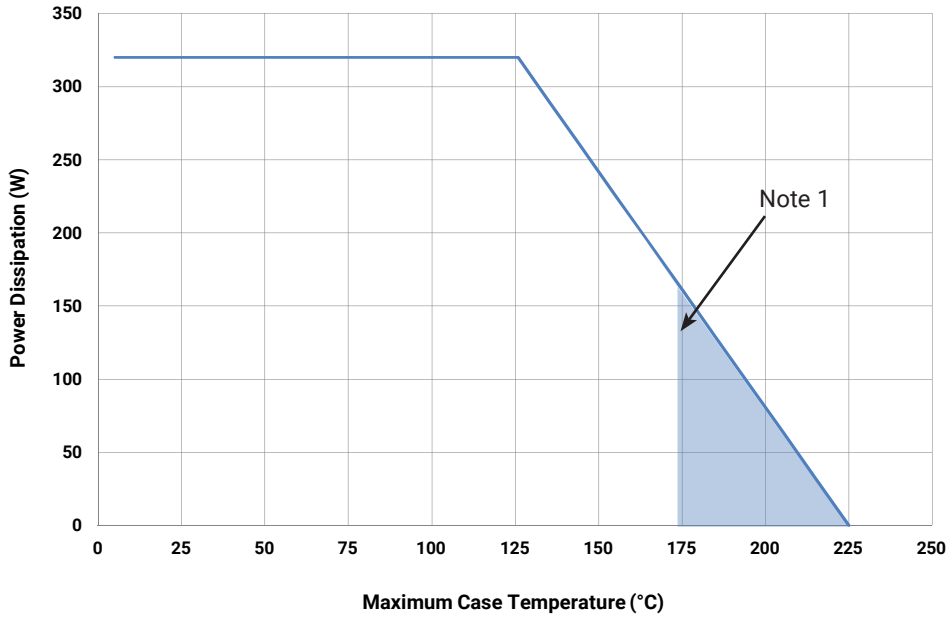
CGHV59350-TB Application Circuit Bill of Materials

Designator	Description	Qty
R1	RES, 5.1OHM, +/- 1%, 1/16W,0603	1
R2	RES, 10OHM, +/- 1%, 1/16W,0603	1
C1,C2	CAP, 5.6pF, +/- 0.25 pF,250V, 0603	2
C3,C8	CAP, 20pF, +/- 0.25 pF,250V, 0603	2
C4,C9	CAP, 470PF, 5%, 100V, 0603, X	2
C5	CAP, 0.1MF, 1206, 250 V, X7R	1
L1	IND, FERRITE, 220 OHM, 0603	1
C10	CAP, 1.0UF, 100V, 10%, X7R, 1210	1
C7	CAP, 5.6pF, +/- 0.25 pF,250V, 0603	1
C11	CAP, 3300 UF, +/-20%, 100V, ELECTROLYTIC	1
C12	CAP, 33 UF, 20%, G CASE	1
J1,J2	CONN, SMA, PANEL MOUNT JACK, FL	2
J3	HEADER RT>PLZ .1CEN LK 9POS	1
J4	CONNECTOR ; SMB, Straight, JACK,SMD	1
W1	CABLE ,18 AWG, 4.2	1
-	PCB, TEST FIXTURE, TACONIC RF35P 20MIL OVER 0.250 COPPER BACK, 2.5 X 3 X 0.26", CGHV59350-TB	1
-	2-56 SOC HD SCREW 1/4 SS	4
-	#2 SPLIT LOCKWASHER SS	4
Q1	CGHV59350	1

CGHV59350 Power Dissipation De-rating Curve

Figure 4. - Transient Power Dissipation De-Rating Curve



Note 1. Area exceeds Maximum Case Temperature (See Page 2).

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4600 Silicon Drive
Durham, North Carolina, USA 27703
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Fax: +1.919.869.2733
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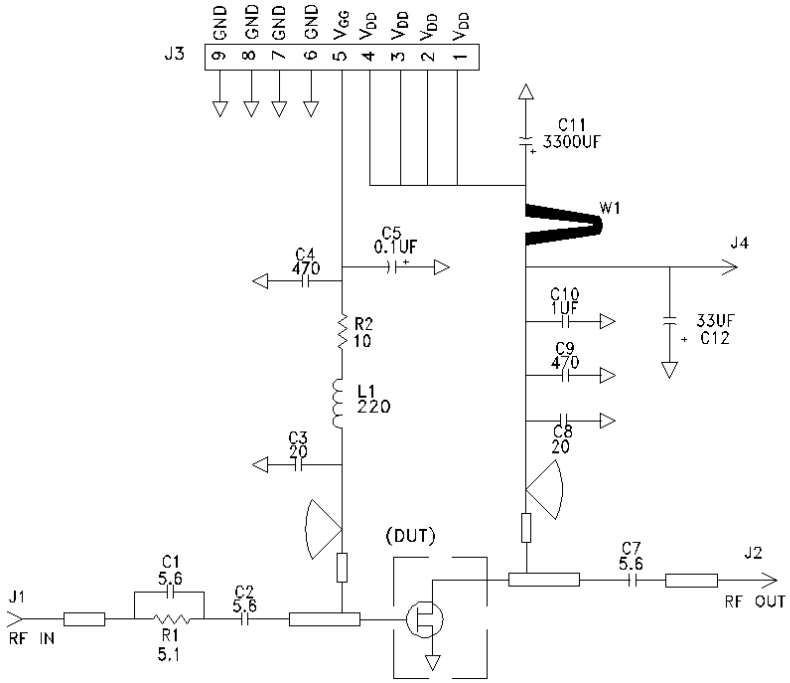
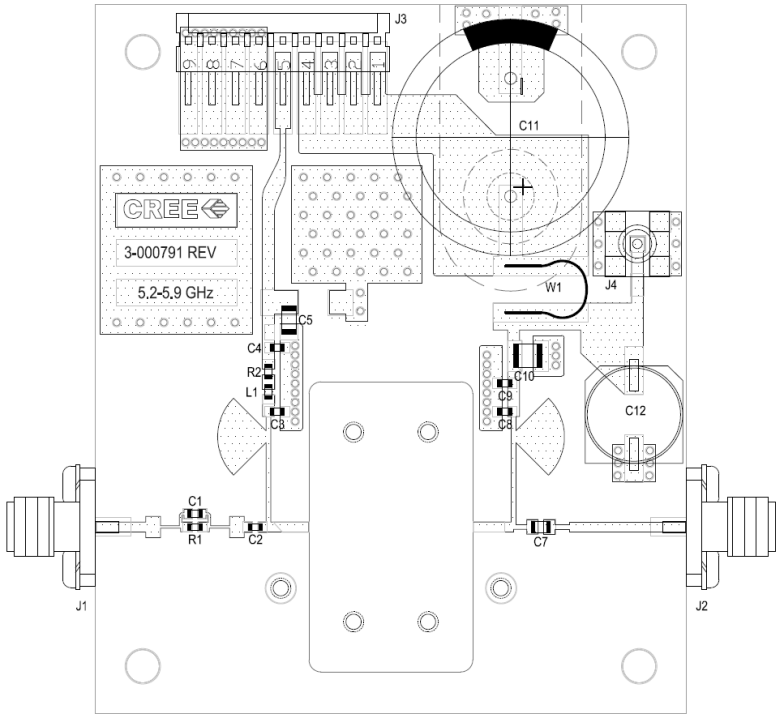
CGHV59350-AMP1 Application Circuit Schematic



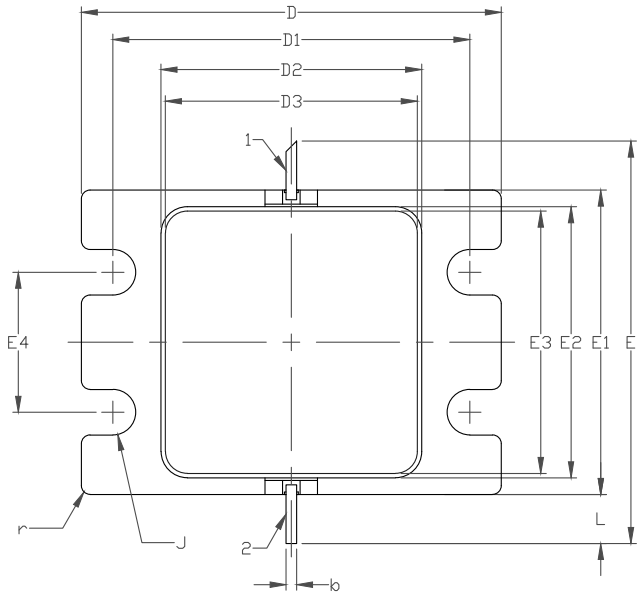
CGHV59350-AMP1 Application Circuit Outline

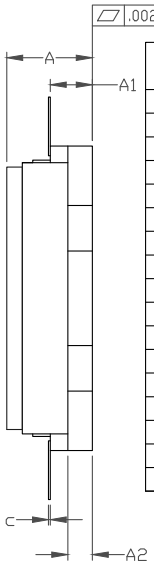


Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
www.cree.com/rf

Product Dimensions CGHV59350F (Package Type — 440217)

NOTES: (UNLESS OTHERWISE SPECIFIED)
1. INTERPRET DRAWING IN ACCORDANCE WITH ANSI Y14.5M-2009
2. ADHESIVE FROM LID MAY EXTEND A MAXIMUM OF .020 BEYOND EDGE OF LID
3. LID MAY BE MISALIGNED TO THE BODY OF PACKAGE BY A MAXIMUM OF .008 IN ANY DIRECTION
4. ALL PLATED SURFACES ARE GOLD OVER NICKEL



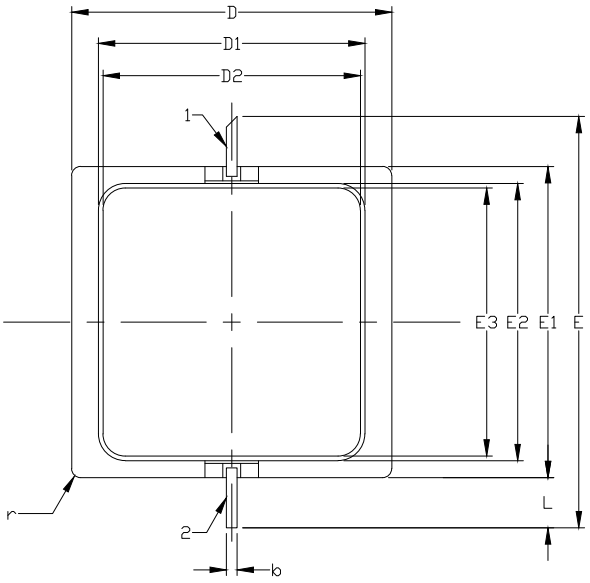


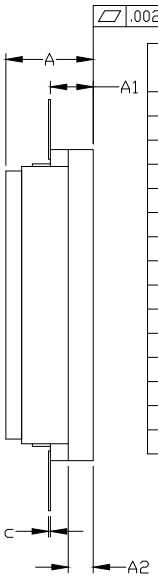
1. GATE
2. DRAIN

DIM	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	0.188	0.198	4.78	5.03	
A1	0.088	0.100	2.24	2.54	2x
A2	0.049	0.061	1.24	1.55	
b	0.022	0.026	0.56	0.66	2x
c	0.002	0.006	0.05	0.15	
D	0.935	0.955	23.75	24.26	
D1	0.797	0.809	20.24	20.55	2x
D2	0.581	0.593	14.76	15.06	
D3	0.563	0.571	14.30	14.50	
E	0.906		23.01		REF
E1	0.679	0.691	17.25	17.55	
E2	0.604	0.616	15.34	15.65	
E3	0.586	0.594	14.88	15.09	
E4	0.309	0.321	7.85	8.15	2x
J	ø0.097	ø0.107	ø2.46	ø2.72	4x
L	0.090	0.130	2.29	3.30	2x
r	0.02 TYP		0.51 TYP		12x

Product Dimensions CGHV59350P (Package Type — 440218)

NOTES: (UNLESS OTHERWISE SPECIFIED)
1. INTERPRET DRAWING IN ACCORDANCE WITH ANSI Y14.5M-2009
2. ADHESIVE FROM LID MAY EXTEND A MAXIMUM OF .020 BEYOND EDGE OF LID
3. LID MAY BE MISALIGNED TO THE BODY OF PACKAGE BY A MAXIMUM OF .008 IN ANY DIRECTION
4. ALL PLATED SURFACES ARE GOLD OVER NICKEL



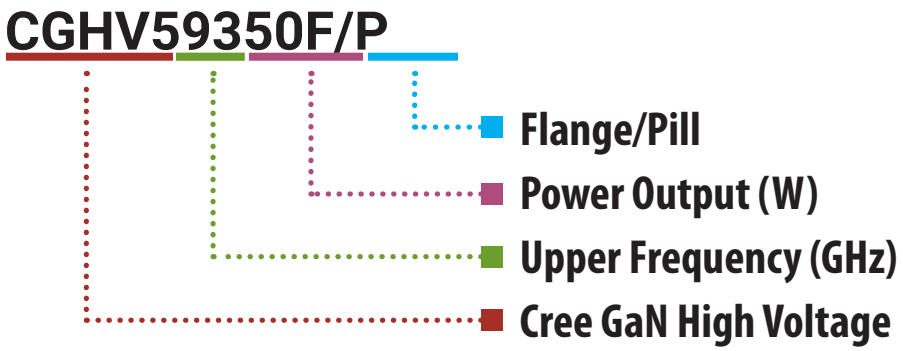


1. GATE
2. DRAIN

DIM	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	0.188	0.198	4.78	5.03	
A1	0.088	0.100	2.24	2.54	2x
A2	0.049	0.061	1.24	1.55	
b	0.022	0.026	0.56	0.66	2x
c	0.002	0.006	0.05	0.15	
D	0.698	0.712	17.72	18.08	
D1	0.581	0.593	14.76	15.06	
D2	0.563	0.571	14.30	14.50	
E	0.906		23.01		REF
E1	0.679	0.691	17.25	17.55	
E2	0.604	0.616	15.34	15.65	
E3	0.586	0.594	14.88	15.09	
J	ø0.097	ø0.107	ø2.46	ø2.72	4x
L	0.090	0.130	2.29	3.30	2x
r	0.02 TYP		0.51 TYP		12x

Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
www.cree.com/rf

Part Number System



Parameter	Value	Units
Upper Frequency[1]	5.9	GHz
Power Output	350	W
Package	Flange/Pill	-

Table 1.

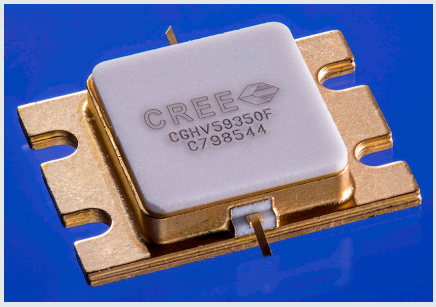
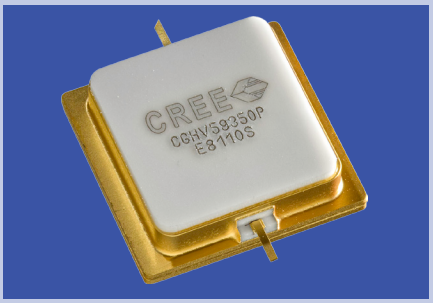
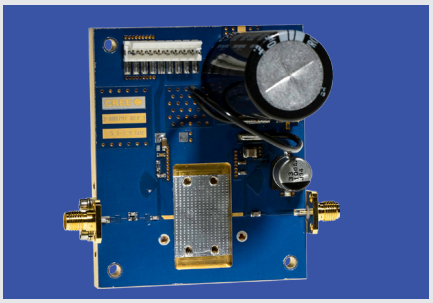
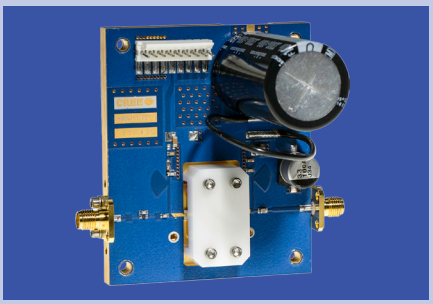
Note[1]: Alpha characters used in frequency code indicate a value greater than 9.9 GHz. See Table 2 for value.

Character Code	Code Value
A	0
B	1
C	2
D	3
E	4
F	5
G	6
H	7
J	8
K	9
Examples:	1A = 10.0 GHz 2H = 27.0 GHz

Table 2.

Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
www.cree.com/rf

Product Ordering Information

Order Number	Description	Unit of Measure	Image
CGHV59350F	GaN HEMT	Each	
CGHV59350P	GaN HEMT	Each	
CGHV59350-TB	Test board without GaN HEMT	Each	
CGHV59350-AMP1	Test board with GaN HEMT installed	Each	

Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
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For more information, please contact:

Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
www.cree.com/rf

Sarah Miller
Marketing & Export
Cree, RF Components
1.919.407.5302

Ryan Baker
Marketing
Cree, RF Components
1.919.407.7816

Tom Dekker
Sales Director
Cree, RF Components
1.919.407.5639

Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
USA Tel: +1.919.313.5300
Fax: +1.919.869.2733
www.cree.com/rf

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- *Подбор аналогов.*
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- *Техническую поддержку проекта.*
- *Защиту от снятия компонента с производства.*
- *Оценку стоимости проекта по компонентам.*
- *Изготовление тестовой платы монтаж и пусконаладочные работы.*

Тел: +7 (812) 336 43 04 (многоканальный)
Email: org@lifeelectronics.ru

www.lifeelectronics.ru